



PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE
(Case No. 05-720-US1)

In the Application of:

Kouvetakis et al.)	Art Unit: 2814
Serial No.: 10/559,979)	
Filed: December 8, 2005)	Examiner: Rao, Shrinivash
For: Sixsnyge1-x-y and related alloy heterostructures)	Confirmation No. 6573
Based on si, ge and sn)	

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Pursuant to 37 C.F.R. Section 1.97 - 1.99, the Applicant wishes to make the following references of record in the above-identified application. This Information Disclosure Statement is in compliance with the continuing duty of candor as set forth in 37 C.F.R. Section 1.56. Copies of the references cited below are enclosed. These references are also listed on the enclosed PTO Form 1449.

In the judgment of the undersigned, portions of the listed references may be material to the Examiner's consideration of the presently pending claims. However, the references have not been reviewed in sufficient detail to make any other representation and, in particular, no representation is intended as to the relative relevance between references, whether cited in this or prior statements. This statement is not a representation that the listed references have effective dates early enough to be "prior art" within the meaning of 35 U.S.C. Section 102 or Section 103.

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This Information Disclosure Statement is being filed:

- ☐ within three months of the filing date of a national application; within three months of the date of entry into the national stage as set forth in 37 C.F.R. § 1.491 in an international application; or before the mailing date of a first Office Action on the merits. 37 C.F.R. § 1.97 (b)
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- ☐ the fee of \$180.00 set forth in 37 C.F.R. § 1.17(p) (see “Fees” below).
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CERTIFICATION

- ☐ The **undersigned** hereby certifies that each item of information contained in the Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign patent application not more than three months prior to the filing of the Information Disclosure Statement.
- ☐ The **undersigned** hereby certifies that no item of information contained in the Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign patent application or, to the knowledge of the person signing the certification after making reasonable inquiry, was known to any individual designated in 37 C.F.R. § 1.56(c) more than three months prior to the filing of the Information Disclosure Statement.

FEES



No fee is owed by the applicant(s).



The **IDS Fee of \$180.00** under 37 C.F.R. § 1.17(p) is enclosed herewith.

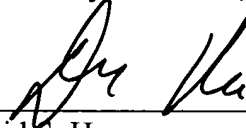
METHOD OF PAYMENT OF FEES



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CERTIFICATE OF MAILING VIA EXPRESS MAIL DELIVERY under 37 C.F.R. § 1.10. I hereby certify that the attached paper of fee is being deposited with the United States Postal Service "Express Mail Post Office to Addressee" Service under 37 C.F.R. § 1.10 on the date indicated above and is addressed to Commissioner for Patents, Box 1450, Alexandria, VA, 22313-1450, on this 8th day of December, 2006. Express Mail No. EV840507720US.

Respectfully submitted,



David S. Harper

Registration No. 42,636

United States Patents

1. Murthy, et al., U.S. Publication No. US 2003-0157787 A1, Published on August 21, 2003.
2. Kouvatakis, et al., U.S. Publication No. US 2006-0134895 A1, Published on June 22, 2006.
3. Kouvatakis, et al., U.S. Publication No. US 2006-0236923 A1, Published on October 26, 2006.
4. Kouvatakis, et al., U.S. Patent No. 6,911,084, Issued on June 28, 2005.
5. Sugawara, et al., U.S. Patent No. 5,532,183, Issued on July 2, 1996.
6. Tang, et al., U.S. Patent No. 5,198,387, Issued on March 30, 1993.
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Foreign Documents

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13. PCT Patent Publication No. WO 2004/114368, published December 29, 2004.
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Commonly owned Co-Pending Applications:

1. Kouvetakis, et al., U.S. Patent Application No. 10/559,980, Filed on December 8, 2005.
2. Kouvetakis, et al., U.S. Patent Application No. 10/559,981, Filed on September 5, 2006. (Projected publication date is January 11, 2007)

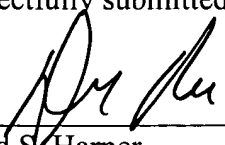
In accordance with MPEP Sections 609 and 707.05(b), it is requested the document cited (including any cited in applicant's specification which is not repeated on the attached Form PTO-1449) be given thorough consideration and that it be cited of record in the prosecution history of the present application by initialing on Form PTO-1449. Such initialing is requested even if the Examiner does not consider a cited document to be sufficiently pertinent to use in a rejection, or otherwise does not consider it to be prior art for any reason, or even if the Examiner does not believe that the guidelines for citation have been fully complied with. This is requested so that each document becomes listed on the face of the patent issuing on the present application.

Respectfully submitted,

Date: _____

12/8/06

By: _____



David S. Harper

Reg. No. 42,636

McDonnell, Boehnen Hulbert & Berghoff LLP

300 South Wacker Drive, Suite #3100

Chicago, IL 60606

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Kouvetakis, et al.

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FORM PTO-1449 (Rev. 2-32)	U.S. Department of Commerce Patent and Trademark Office	Atty. Docket No. 05-720-US1	Serial No. 10/559,979
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)		Applicant: Kouvetakis, et al.	
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COMMONLY OWNED CO-PENDING APPLICATIONS

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(Use several sheets if necessary)

Applicant:

Kouvetakis, et al.

Filing Date:

December 8, 2005

Group:

2814

	1.	Kouvetakis, et al., U.S. Patent Application No. 10/559,980, Filed on December 8, 2005.
	2.	Kouvetakis, et al., U.S. Patent Application No. 10/559,981, Filed on September 5, 2006 (Projected Publication date is January 11, 2007).

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